





FIG.4

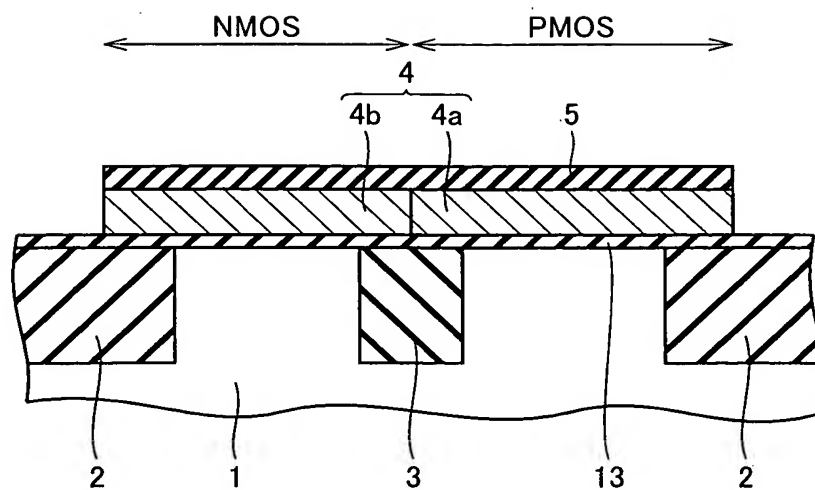


FIG.5

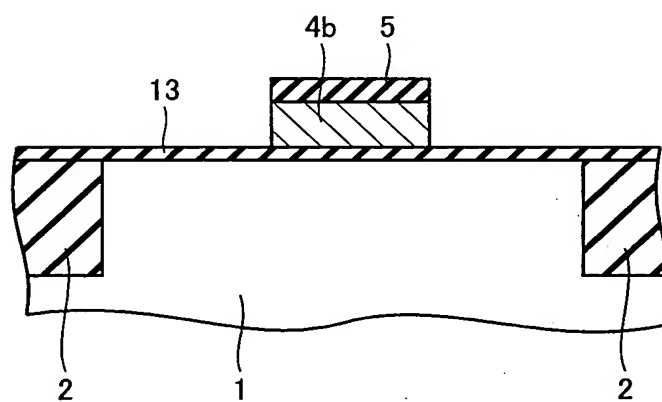


FIG.6

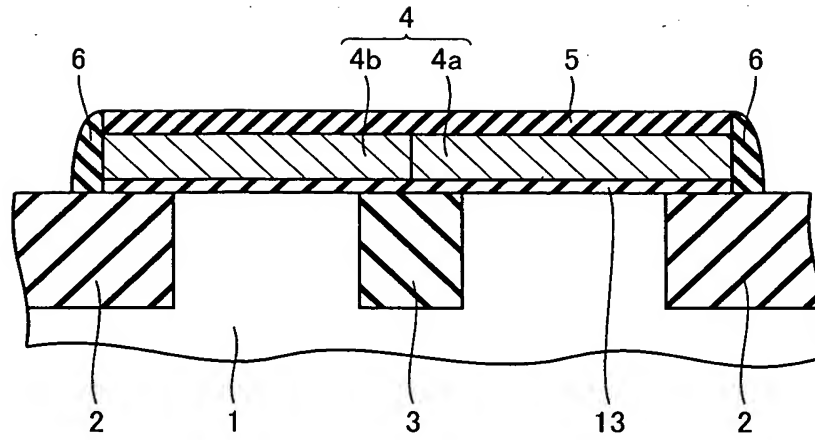
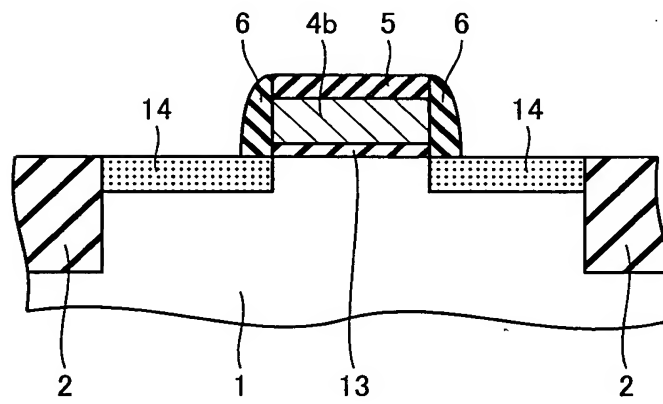


FIG.7



A detailed cross-sectional view of a multi-layered structure. The structure consists of several layers and components labeled with numbers 1 through 13. At the base is a wavy line labeled 1. Above this are three rectangular blocks labeled 2, separated by a central gap. The blocks 2 are supported by a layer labeled 4, which is divided into two parts, 4a and 4b, by a vertical line labeled 7. Above layer 4 is a layer labeled 13. On top of layer 13 are two rectangular blocks labeled 5, separated by a central gap. The blocks 5 are supported by a layer labeled 6. Above layer 6 is a layer labeled 8. The top surface of the structure is a wavy line labeled 9. The central gap between the blocks 5 is labeled 3. The central gap between the blocks 2 is labeled 4.

This cross-sectional view shows a semiconductor device with a central raised region. The device consists of a substrate (2) with a central layer (13) and side layers (14). A central layer (5) is on top of the central layer (13), and a central layer (8) is on top of the central layer (5). A central layer (6) is on top of the central layer (8). The central region is surrounded by a central layer (6) and a central layer (8). The central region is surrounded by a central layer (6) and a central layer (8).

FIG.10

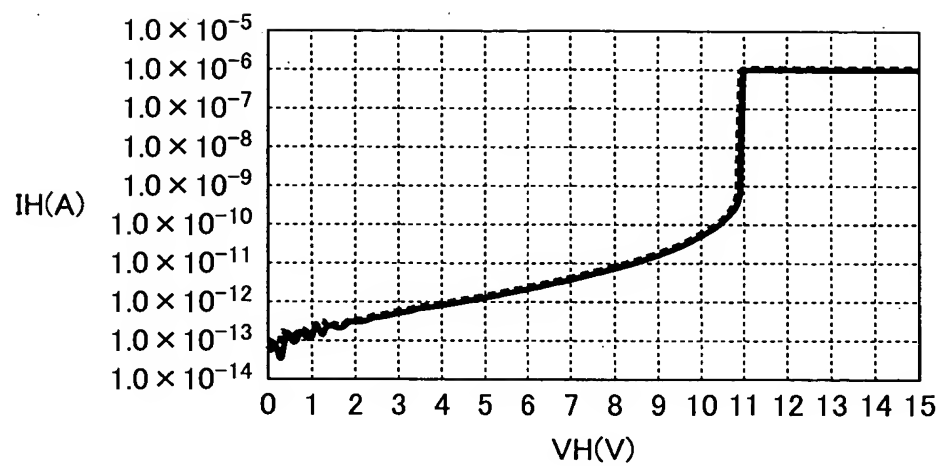


FIG.11 PRIOR ART

